

“Insights into Ni-filament formation in unipolar-switching Ni/HfO₂/TiN resistive random access memory device”. Chen YY, Pourtois G, Adelmann C, Goux L, Govoreanu B, Degreave R, Jurczak M, Kittl JA, Groeseneken G, Wouters DJ, Applied physics letters **100**, 113513 (2012). <http://doi.org/10.1063/1.3695078>